



DMMT5401

MATCHED PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

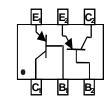
- **Epitaxial Planar Die Construction**
- Complementary NPN Type Available (DMMT5551)
- Ideal for Low Power Amplification and Switching
- Intrinsically Matched PNP Pair (Note 1)
- 2% Matched Tolerance, hFE, VCE(SAT), VBE(SAT)
- Lead Free/RoHS Compliant (Note 4)
- "Green" Device (Note 5 and 6)

В

SOT-26 Dim Min Max Тур 0.50 Α 0.35 0.38 В 1.50 1.70 1.60 С 2.70 3.00 2.80 D 0.95 F 0.55 Н 3.00 2.90 3.10 J 0.10 0.05 0.013 1.30 1.10 K 1.00 L 0.55 0.40 0.35 М 0.10 0.20 0.15 0° 8° All Dimensions in mm

Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound, Note 6. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Copper leadframe).
- Marking Information: K4S, See Page 3
- Ordering & Date Code Information: See Page 3
- Weight: 0.006 grams (approximate)



Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-160	V
Collector-Emitter Voltage	V _{CEO}	-150	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous (Note 2)	I _C	-200	mA
Power Dissipation (Note 2, 3)	P _d	300	mW
Thermal Resistance, Junction to Ambient (Note 2)	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Notes:

- Built with adjacent die from a single wafer. 1.
- Device mounted on FR5 PCB: 1.0 x 0.75 x 0.62 in.; pad layout as shown on suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 3. Maximum combined dissipation.
- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

 Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

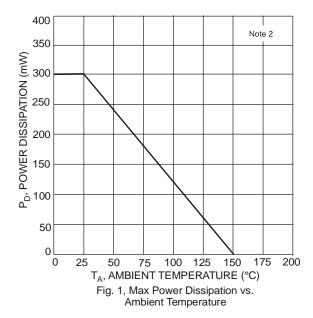


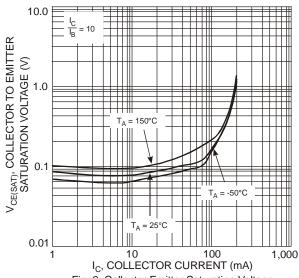
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition				
OFF CHARACTERISTICS (Note 7)									
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-160		٧	$I_C = -100 \mu A, I_E = 0$				
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-150		٧	$I_C = -1.0 \text{mA}, I_B = 0$				
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0		٧	$I_E = -10\mu A, I_C = 0$				
Collector Cutoff Current	I _{CBO}		-50	nA μA	$V_{CB} = -120V, I_{E} = 0$ $V_{CB} = -120V, I_{E} = 0, T_{A} = 100^{\circ}C$				
Emitter Cutoff Current	I _{EBO}	_	-50	nA	$V_{EB} = -3.0V, I_{C} = 0$				
ON CHARACTERISTICS (Note 7)									
DC Current Gain (Note 8)	h _{FE}	50 60 50	 240 	_	$I_C = -1.0$ mA, $V_{CE} = -5.0$ V $I_C = -10$ mA, $V_{CE} = -5.0$ V $I_C = -50$ mA, $V_{CE} = -5.0$ V				
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	-0.2 -0.5	V	$I_C = -10 \text{mA}, I_B = -1.0 \text{mA}$ $I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$				
Base-Emitter Saturation Voltage	V _{BE(SAT)}		-1.0	V	$I_C = -10 \text{mA}, I_B = -1.0 \text{mA}$ $I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$				
SMALL SIGNAL CHARACTERISTICS									
Output Capacitance	C_{obo}	_	6.0	pF	$V_{CB} = -10V$, $f = 1.0MHz$, $I_E = 0$				
Small Signal Current Gain	h _{fe}	40	200		$V_{CE} = -10V, I_{C} = -1.0mA,$ f = 1.0kHz				
Current Gain-Bandwidth Product	f⊤	100	300	MHz	$V_{CE} = -10V, I_{C} = -10mA,$ f = 100MHz				
Noise Figure	NF		8.0	dB	V_{CE} = -5.0V, I_{C} = -200 μ A, R_{S} = 10 Ω , f = 1.0kHz				

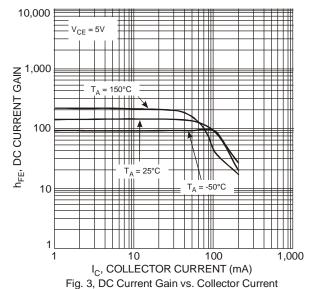
Notes:

- Short duration pulse test used to minimize self-heating effect. The DC Current Gain, h_{FE} , (matched at $I_C = -10$ mA and $V_{CE} = -5$ V) Collector Emitter Saturation Voltage, $V_{CE(SAT)}$, and Base Emitter Saturation Voltage, $V_{BE(SAT)}$ are matched with typical matched tolerances of 1% and maximum of 2%.









1.0 $V_{BE(ON)}$, BASE EMITTER VOLTAGE (V) 0.9 T_A = -50°C 8.0 0.7 0.6 T_A = 25°C 0.5 0.4 $T_A = 150$ °C 0.3 0.2 0.1 $\begin{array}{c} 1.0 & 10 \\ \text{I}_{\text{C}}, \text{COLLECTOR CURRENT (mA)} \end{array}$ 0.1 100 Fig. 4, Base Emitter Voltage vs. Collector Current

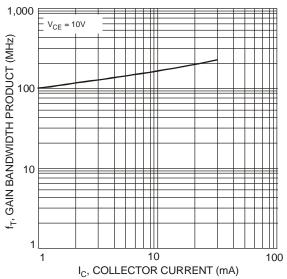


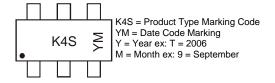
Fig. 5, Gain Bandwidth Product vs. Collector Current

Ordering Information (Note 6 & 9)

Device	Packaging	Shipping
DMMT5401-7-F	SOT-26	3000/Tape & Reel

9. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



Date Code Key

Year	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	R	S	T	U	V	W	Х	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



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